74HC4520; 74HCT4520

Dual 4-bit synchronous binary counter

Rev. 3 — 4 December 2014 Product data sheet

1. General description

The 74HC4520; 74HCT4520 are dual 4-bit internally synchronous binary counters with two clock inputs (nCP0 and n$\overline{CP}$1). They have buffered outputs from all 4 bit positions (nQ0 to nQ3) and an asynchronous master reset input (nMR). The counter advances on the LOW-to-HIGH transition of nCP0 when n$\overline{CP}$1 is HIGH. It also advances on the HIGH-to-LOW transition of n$\overline{CP}$1 when nCP0 is LOW. Either nCP0 or n$\overline{CP}$1 may be used as the clock input to the counter. The other clock input may be used as a clock enable input. A HIGH on nMR, resets the counter (nQ0 to nQ3 = LOW) independent of nCP0 and n$\overline{CP}$1. Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

2. Features and benefits

- Complies with JEDEC standard no. 7A
- Input levels:
  - For 74HC4520: CMOS level
  - For 74HCT4520: TTL level
- ESD protection:
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from −40 °C to +85 °C and −40 °C to +125 °C

3. Applications

- Multistage synchronous counting
- Multistage asynchronous counting
- Frequency dividers

4. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC4520N	−40 °C to +125 °C	DIP16	plastic dual in-line package; 16 leads (300 mil)	SOT38-4
74HCT4520N				
74HC4520D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT4520D				
74HC4520DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT4520DB				
74HC4520PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

5. Functional diagram

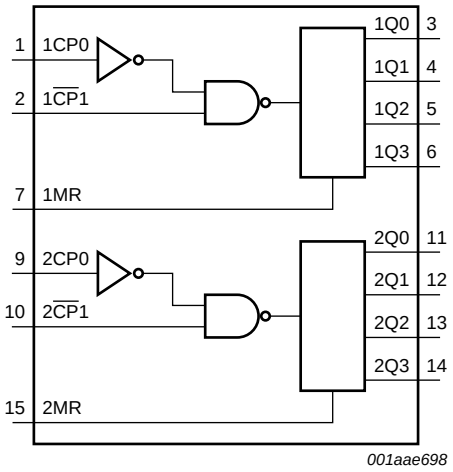

Fig 1. Functional diagram

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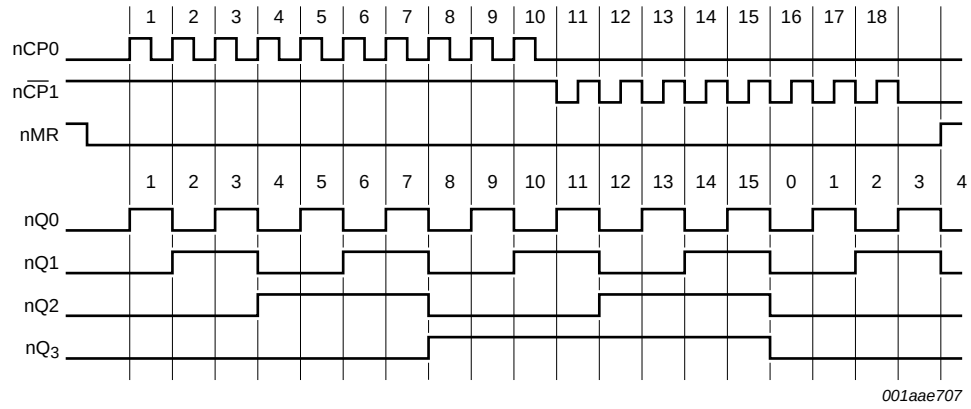

Fig 2. Timing diagram

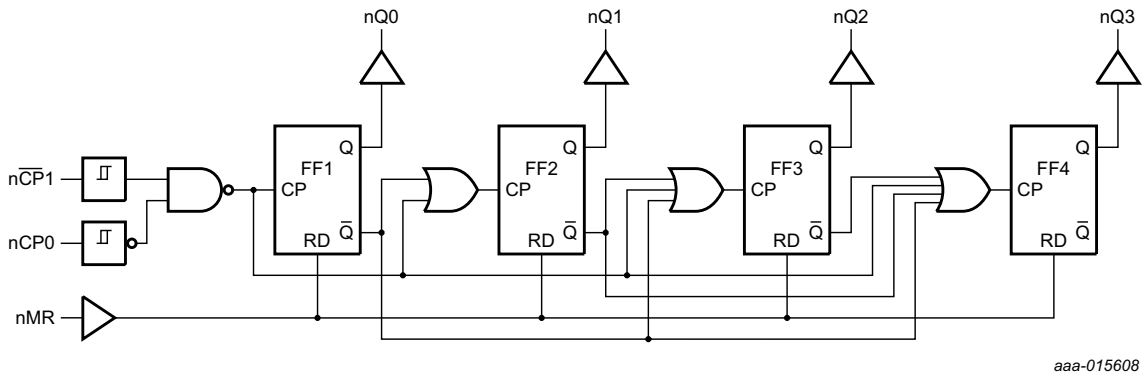

Fig 3. Logic diagram for one counter

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6. Pinning information

6.1 Pinning

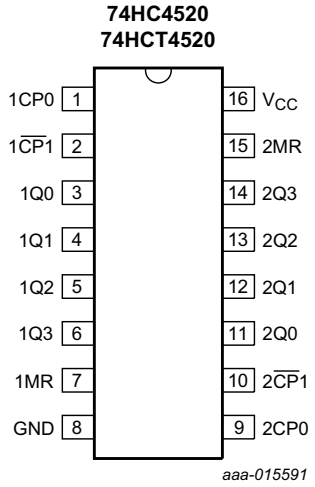

Fig 4. Pin configuration DIP16

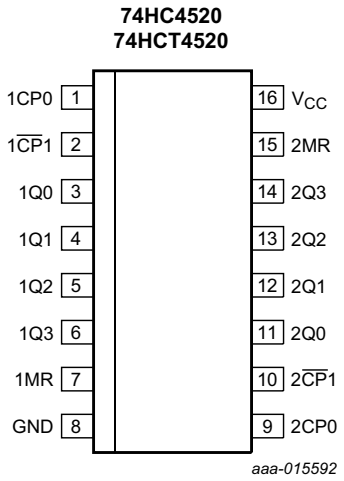

Fig 5. Pin configuration SO16

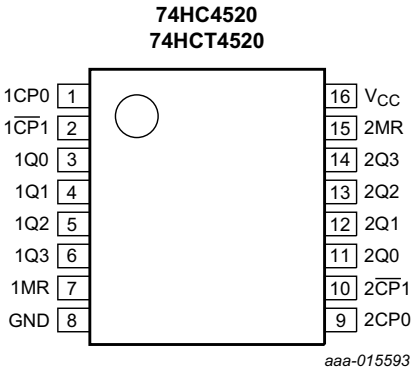

Fig 6. Pin configuration TSSOP16 and SSOP16

6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP0, 2CP0	1, 9	clock input (LOW-to-HIGH edge-triggered)
$1\overline{CP}1$, $2\overline{CP}1$	2, 10	clock input (HIGH-to-LOW edge-triggered)
1Q0 to 1Q3	3, 4, 5, 6	output
1MR, 2MR	7, 15	asynchronous master reset input (active HIGH)
GND	8	ground (0 V)
2Q0 to 2Q3	11, 12, 13, 14	output
V_{CC}	16	supply voltage

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7. Functional description

Table 3. Function table[1]

nCP0	$\overline{nCP1}$	nMR	Mode
↑	H	L	counter advances
L	↓	L	counter advances
↓	X	L	no change
X	↑	L	no change
↑	L	L	no change
H	↓	L	no change
X	X	H	nQ0 to nQ3 = LOW

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; ↑ = positive-going transition; ↓ = negative-going transition.

8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		−0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	±20	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	-	±20	mA
I_O	output current	$V_O = -0.5$ V to $V_{CC} + 0.5$ V	-	±25	mA
I_{CC}	supply current		-	50	mA
I_{GND}	ground current		−50	-	mA
T_{stg}	storage temperature		−65	+150	°C
P_{tot}	total power dissipation	DIP16 package [1]	-	750	mW
		SO16 package [1]	-	500	mW
		(T)SSOP16 package [1]	-	500	mW

[1] For DIP16 packages: above 70 °C the value of P_{tot} derates linearly at 12 mW/K.
For SO16 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.
For (T)SSOP16 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

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9. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC4520			74HCT4520			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		−40	+25	+125	−40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V_{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V_{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4520										
V_{IH}	HIGH-level input voltage	V_{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V_{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V_{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V_{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V_{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = −20 μA; V_{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I_O = −20 μA; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = −20 μA; V_{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I_O = −4.0; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_O = −5.2; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}								
		I_O = 20 μA; V_{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 20 μA; V_{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_O = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 6.0 V	-	-	8.0	-	80.0	-	160.0	μA

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Table 6. Static characteristics *…continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
C_I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT4520										
V_{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = –20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		I_O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}; V_{CC} = 4.5 V								
		I_O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I_O = 4.0 mA	-	0.15	0.26	-	0.33	-	0.4	V
I_I	input leakage current	V_I = V_{CC} or GND; V_{CC} = 5.5 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I_{CC}	supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	-	8.0	-	80.0	-	160.0	μA
ΔI_{CC}	additional supply current	per input pin; V_I = V_{CC} – 2.1 V; other inputs at V_{CC} or GND; V_{CC} = 4.5 V to 5.5 V; I_O = 0 A								
		pin nCP0, $n\overline{CP1}$	-	80	288	-	360	-	392	μA
		pin nMR	-	150	540	-	675	-	735	μA
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

11. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 8.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC4520										
t_{pd}	propagation delay	nCP0 to nQn; see Figure 7 [1]								
		V_{CC} = 2.0 V	-	77	240	-	300	-	360	ns
		V_{CC} = 4.5 V	-	28	48	-	60	-	72	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	24	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	22	41	-	51	-	61	ns
		$n\overline{CP1}$ to nQn; see Figure 7 [1]								
		V_{CC} = 2.0 V	-	77	240	-	300	-	360	ns
		V_{CC} = 4.5 V	-	28	48	-	60	-	72	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	24	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	22	41	-	51	-	61	ns

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Table 7. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 8.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PHL}	HIGH to LOW propagation delay	nMR to nQn; see Figure 7								
		V_{CC} = 2.0 V	-	44	150	-	190	-	225	ns
		V_{CC} = 4.5 V	-	16	30	-	38	-	45	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	13	-	-	-	-	-	ns
		V_{CC} = 6.0 V	-	13	26	-	33	-	38	ns
t_t	transition time	nQn; see Figure 7 [2]								
		V_{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V_{CC} = 6.0 V	-	6	13	-	16	-	19	ns
t_W	pulse width	nCP0, n$\overline{CP}$1 HIGH or LOW; see Figure 7								
		V_{CC} = 2.0 V	80	22	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	8	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	6	-	17	-	20	-	ns
		nMR HIGH; see Figure 7								
		V_{CC} = 2.0 V	120	39	-	150	-	180	-	ns
		V_{CC} = 4.5 V	24	14	-	30	-	36	-	ns
		V_{CC} = 6.0 V	20	11	-	26	-	31	-	ns
t_{rec}	recovery time	nMR to nCP0, n$\overline{CP}$1; see Figure 7								
		V_{CC} = 2.0 V	0	–28	-	0	-	0	-	ns
		V_{CC} = 4.5 V	0	–10	-	0	-	0	-	ns
		V_{CC} = 6.0 V	0	–8	-	0	-	0	-	ns
t_{su}	set-up time	nCP0 to n$\overline{CP}$1; n$\overline{CP}$1 to nCP0; see Figure 7								
		V_{CC} = 2.0 V	80	14	-	100	-	120	-	ns
		V_{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		V_{CC} = 6.0 V	14	4	-	17	-	20	-	ns
f_{max}	maximum frequency	nCP0, n$\overline{CP}$1; see Figure 7								
		V_{CC} = 2.0 V	6	19	-	4.8	-	4	-	MHz
		V_{CC} = 4.5 V	30	58	-	24	-	20	-	MHz
		V_{CC} = 5.0 V; C_L = 15 pF	-	68	-	-	-	-	-	MHz
		V_{CC} = 6.0 V	35	69	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC}; V_{CC} = 5 V; f_i = 1 MHz [3]	-	29	-	-	-	-	-	pF
74HCT4520										
t_{pd}	propagation delay	nCP0 to nQn; see Figure 7 [1]								
		V_{CC} = 4.5 V	-	28	53	-	66	-	80	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	24	-	-	-	-	-	ns
		n$\overline{CP}$1 to nQn; see Figure 7 [1]								
		V_{CC} = 4.5 V	-	25	53	-	66	-	80	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	24	-	-	-	-	-	ns

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Table 7. Dynamic characteristics *…continued*

Voltages are referenced to GND (ground = 0 V); C_L = 50 pF unless otherwise specified; for test circuit, see Figure 8.

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
t_{PHL}	HIGH to LOW propagation delay	nMR to nQn; see Figure 7								
		V_{CC} = 4.5 V	-	16	35	-	44	-	53	ns
		V_{CC} = 5.0 V; C_L = 15 pF	-	13	-	-	-	-	-	ns
t_t	transition time	nQn; see Figure 7 [2]								
		V_{CC} = 4.5 V	-	7	15	-	19	-	22	ns
t_W	pulse width	nCP0, n$\overline{CP}$1 HIGH or LOW; see Figure 7								
		V_{CC} = 4.5 V	20	10	-	25	-	30	-	ns
		nMR HIGH; see Figure 7								
		V_{CC} = 4.5 V	20	12	-	25	-	30	-	ns
t_{rec}	recovery time	nMR to nCP0, n$\overline{CP}$1; see Figure 7								
		V_{CC} = 4.5 V	0	–8	-	0	-	0	-	ns
t_{su}	set-up time	nCP0 to n$\overline{CP}$1; n$\overline{CP}$1 to nCP0; see Figure 7								
		V_{CC} = 4.5 V	16	6	-	20	-	24	-	ns
f_{max}	maximum frequency	nCP0, n$\overline{CP}$1; see Figure 7								
		V_{CC} = 4.5 V	30	58	-	24	-	20	-	MHz
		V_{CC} = 5.0 V; C_L = 15 pF	-	64	-	-	-	-	-	MHz
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC} − 1.5 V; V_{CC} = 5 V; f_i = 1 MHz [3]	-	24	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH}.

[2] t_t is the same as t_{THL} and t_{TLH}.

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW):
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

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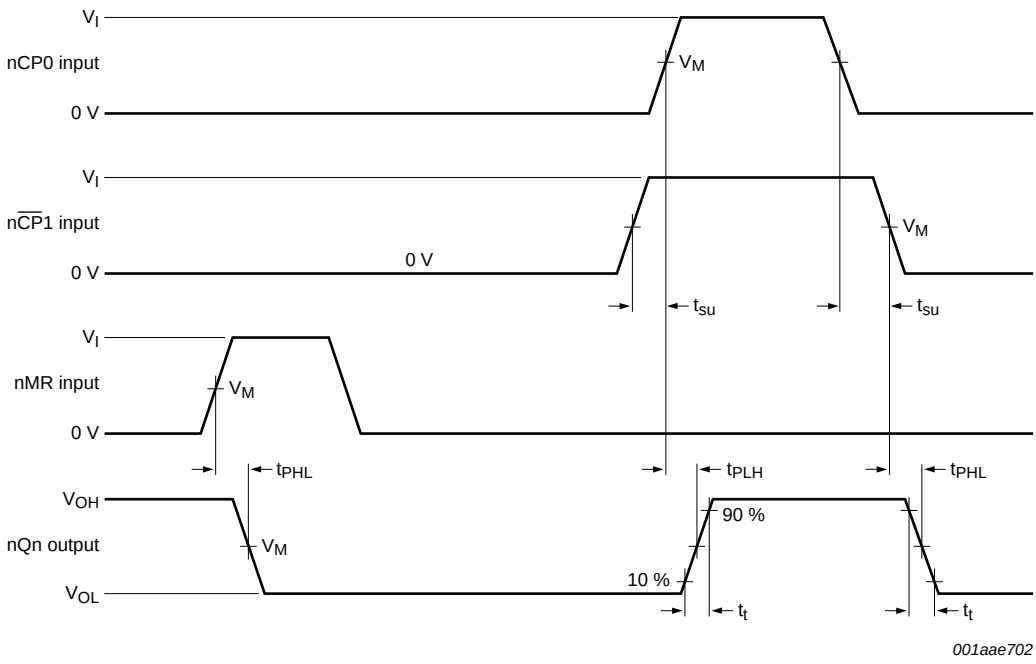
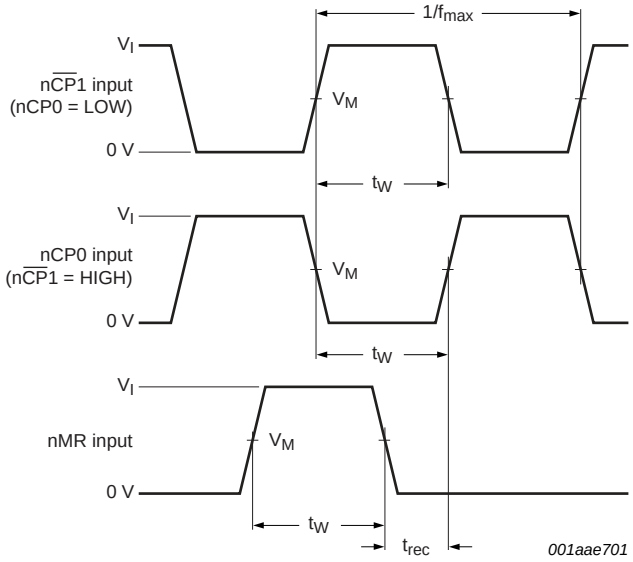
12. Waveforms



a. nCP0 and nCP1 set-up times, propagation delays and output transition times



b. nMR recovery time, minimum nCP0, nCP1, nMR pulse widths and maximum frequency

Measurement points are given in Table 8.

The logic levels V_{OH} and V_{OL} are typical output voltage levels that occur with the output load.

Fig 7. Waveforms showing measurements for switching times

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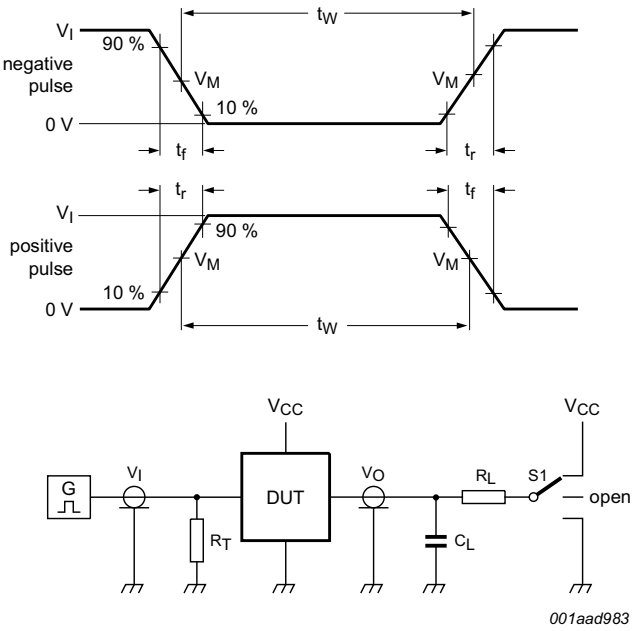
Table 8. Measurement points

Type	Input		Output
	V_M	V_I	V_M
74HC4520	$0.5 \times V_{CC}$	GND to V_{CC}	$0.5 \times V_{CC}$
74HCT4520	1.3 V	GND to 3 V	1.3 V



Test data is given in Table 9.

Test circuit definitions:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

C_L = Load capacitance including jig and probe capacitance

R_L = Load resistance.

S1 = Test selection switch

Fig 8. Test circuit for measuring switching times

Table 9. Test data

Type	Input		Load		S1 position
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}
74HC4520	V_{CC}	6 ns	15 pF, 50 pF	1 kΩ	open
74HCT4520	3 V	6 ns	15 pF, 50 pF	1 kΩ	open

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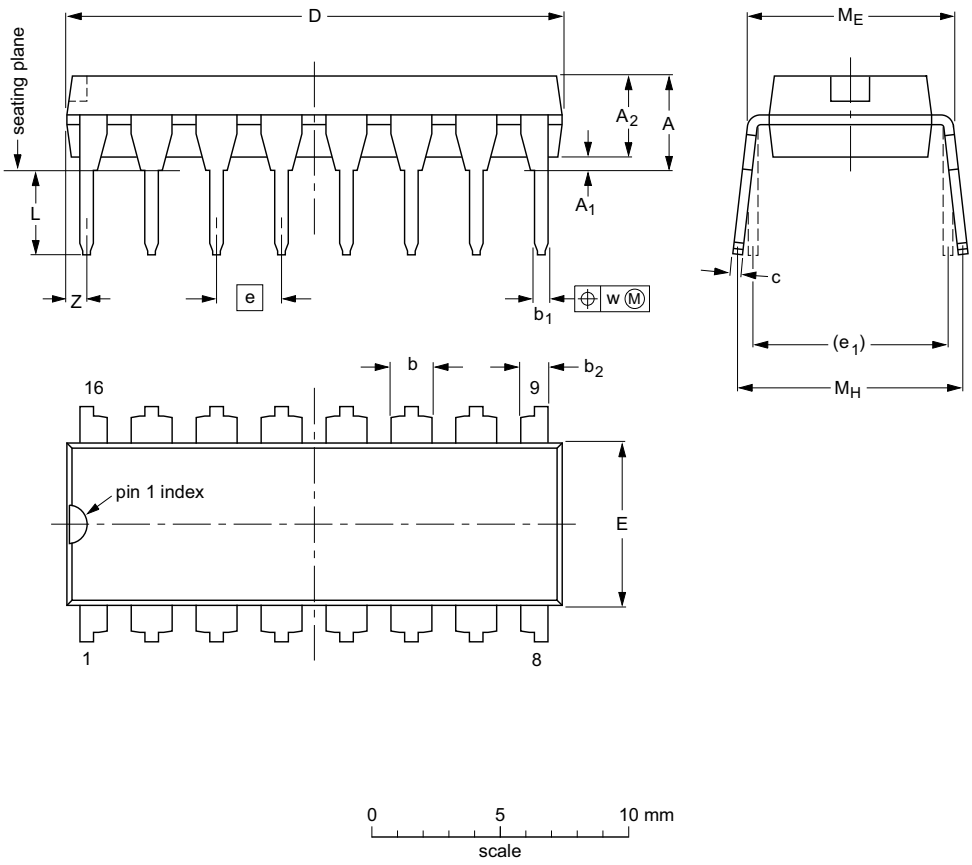
13. Package outline

DIP16: plastic dual in-line package; 16 leads (300 mil) **SOT38-4**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1 min.	A_2 max.	b	b_1	b_2	c	D (1)	E (1)	e	e_1	L	M_E	M_H	w	Z (1) max.
mm	4.2	0.51	3.2	1.73 1.30	0.53 0.38	1.25 0.85	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	0.76
inches	0.17	0.02	0.13	0.068 0.051	0.021 0.015	0.049 0.033	0.014 0.009	0.77 0.73	0.26 0.24	0.1	0.3	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.03

Note

1. Plastic or metal protrusions of 0.25 mm (0.01 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT38-4						~~95-01-14~~ 03-02-13

Fig 9. Package outline SOT38-4 (DIP16)

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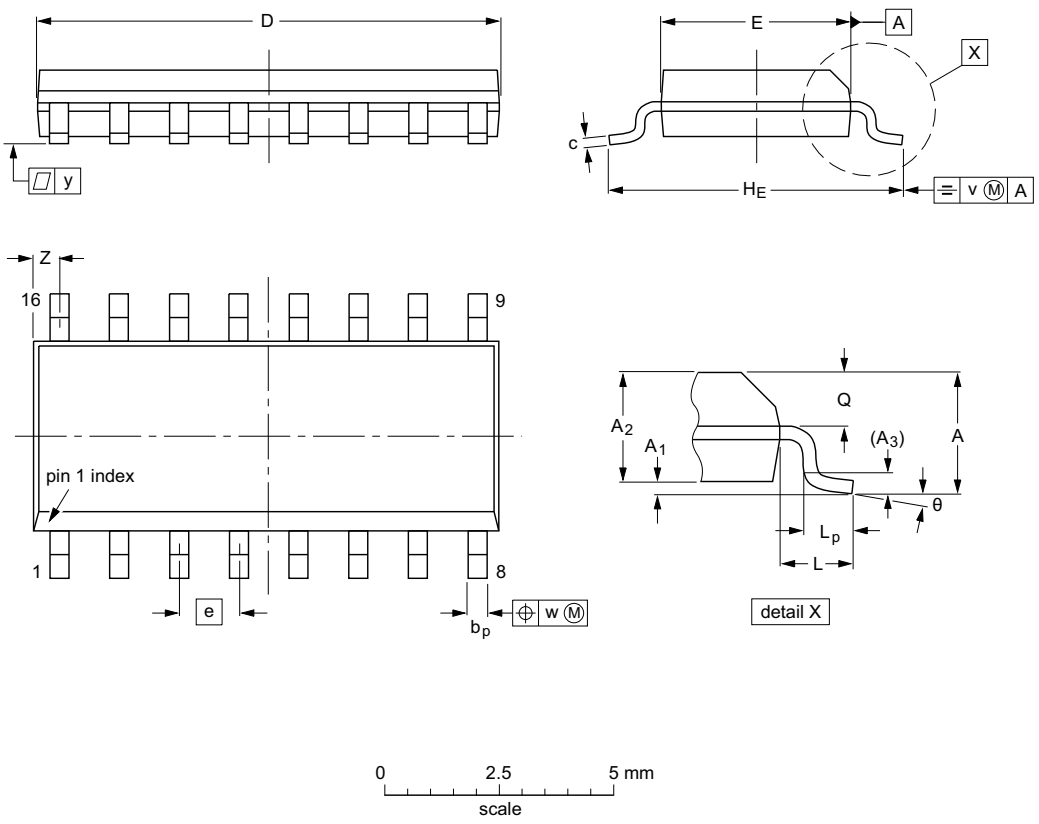
SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	$D^{(1)}$	$E^{(1)}$	e	H_E	L	L_p	Q	v	w	y	$Z^{(1)}$	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 10. Package outline SOT109-1 (SO16)

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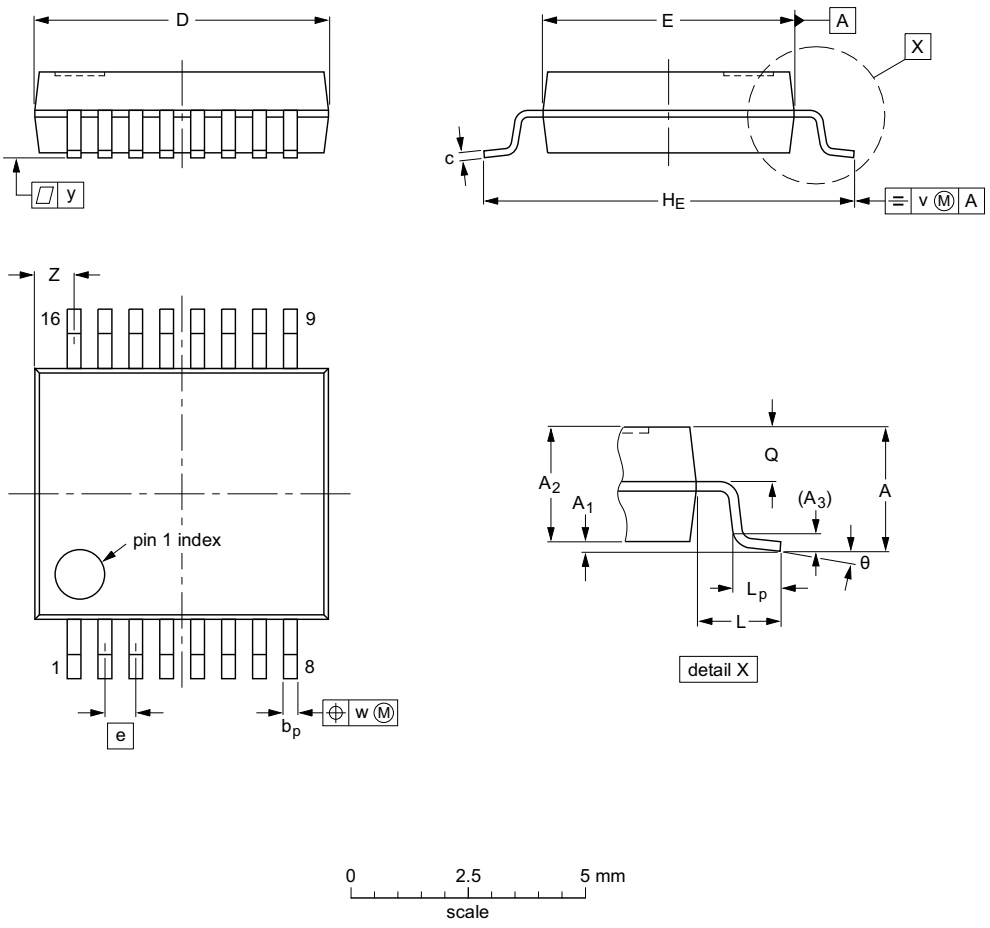
SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm **SOT338-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	2	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.00 0.55	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT338-1		MO-150				~~99-12-27~~ 03-02-19

Fig 11. Package outline SOT338-1 (SSOP16)

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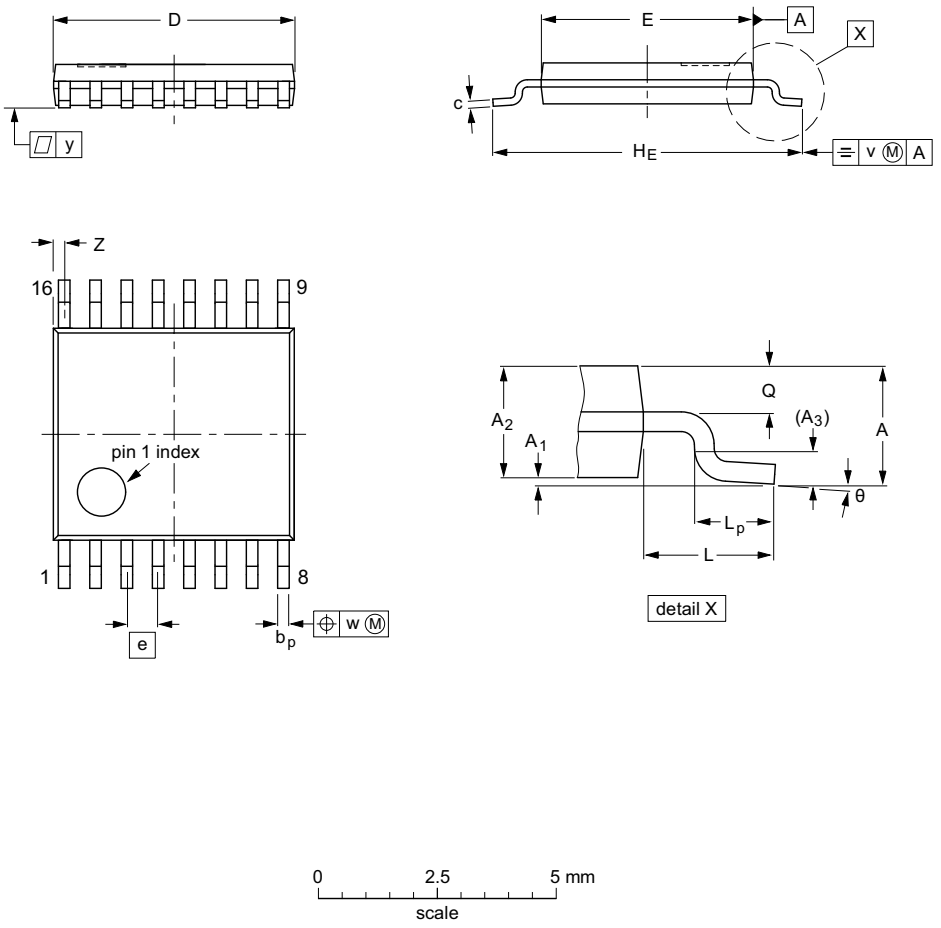
TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 12. Package outline SOT403-1 (TSSOP16)

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14. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT4520 v.3	20141204	Product data sheet	-	74HC_HCT4520_CNV v.2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT4520_CNV v.2	19930927	Product specification	-	-

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16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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